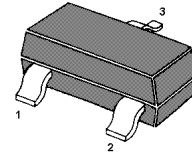


MMBTSC3838

NPN Silicon Epitaxial Planar Transistor

for high frequency amplifier application



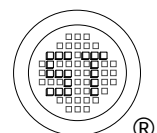
1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	20	V
Collector Emitter Voltage	V_{CEO}	11	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	50	mA
Collector Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 5\text{ mA}$	h_{FE}	56	-	160	-
Current Gain Group R S	h_{FE}	120	-	240	-
Collector Base Cutoff Current at $V_{CB} = 10\text{ V}$	I_{CBO}	-	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 2\text{ V}$	I_{EBO}	-	-	500	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	20	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	11	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	3	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_E = 10\text{ mA}$, $f = 500\text{ MHz}$	f_T	-	3.2	-	GHz
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	1.5	pF



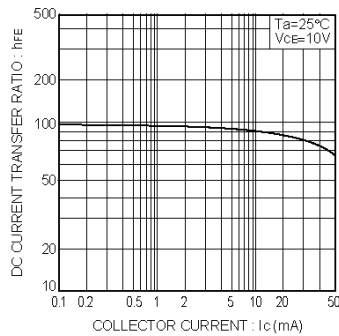


Fig.1 DC current gain vs. collector current

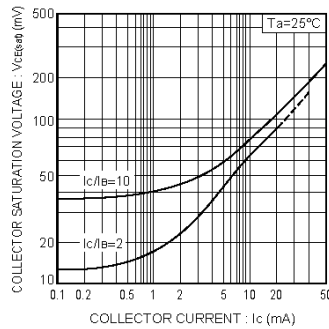


Fig.2 Collector-emitter saturation voltage vs. collector current

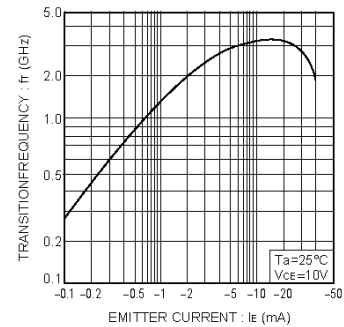


Fig.3 Gain bandwidth product vs. emitter current

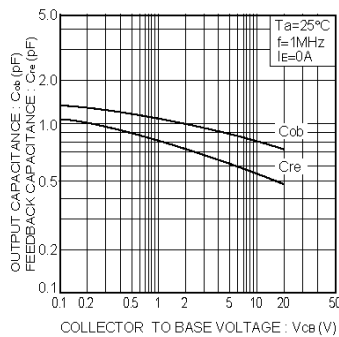


Fig.4 Capacitance vs. reverse bias voltage

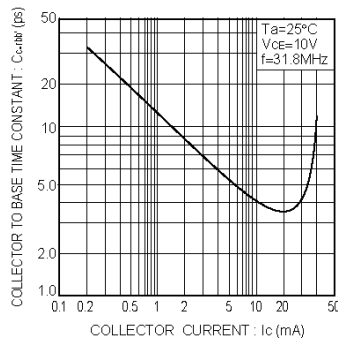


Fig.5 Collector to base time constant vs. collector current

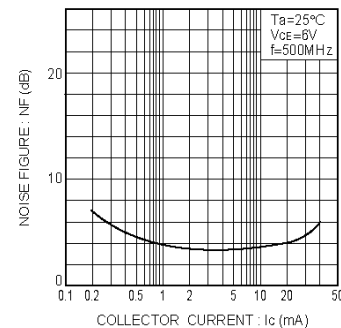


Fig.6 Noise factor vs. collector current characteristics

